



Figure 2c

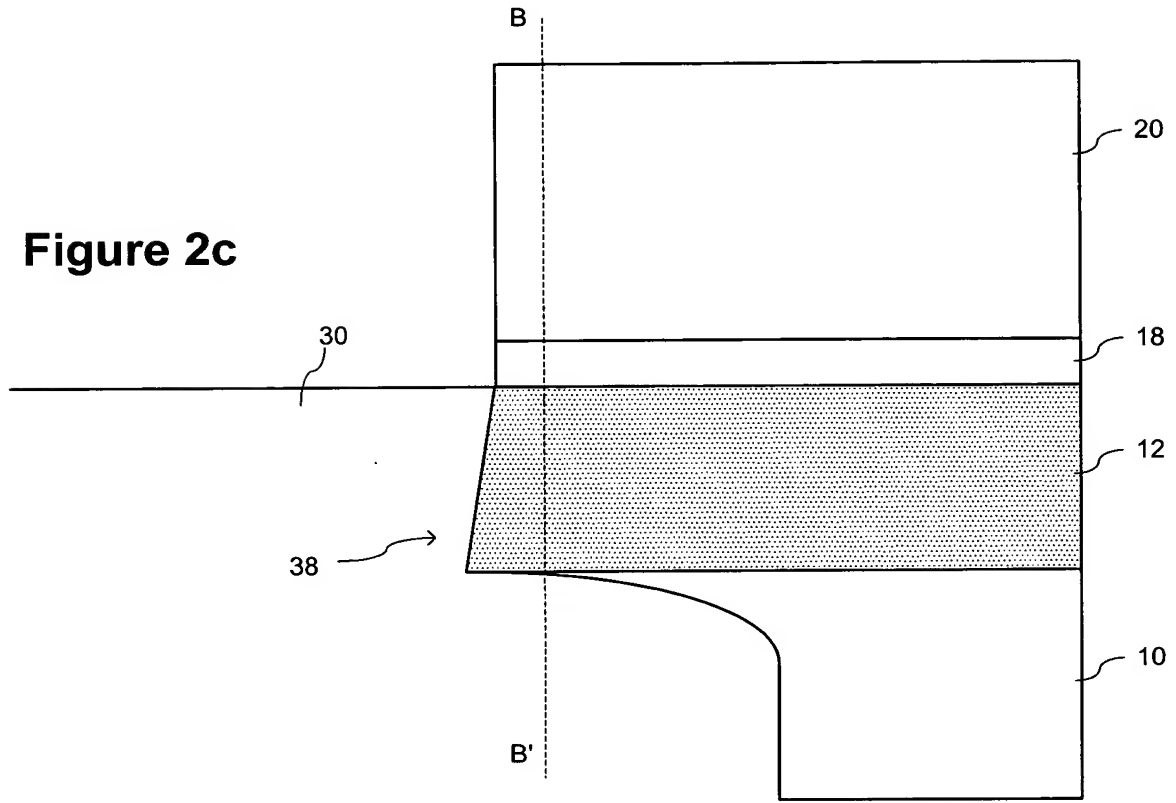
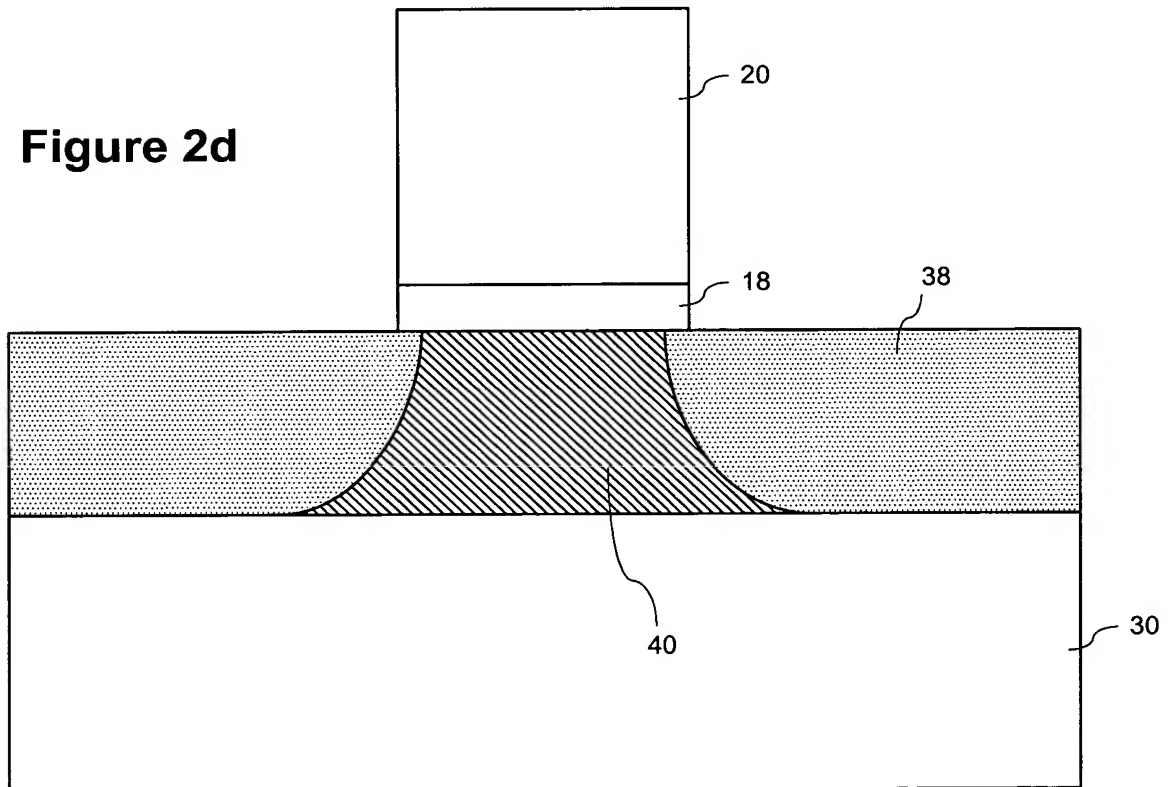


Figure 2d



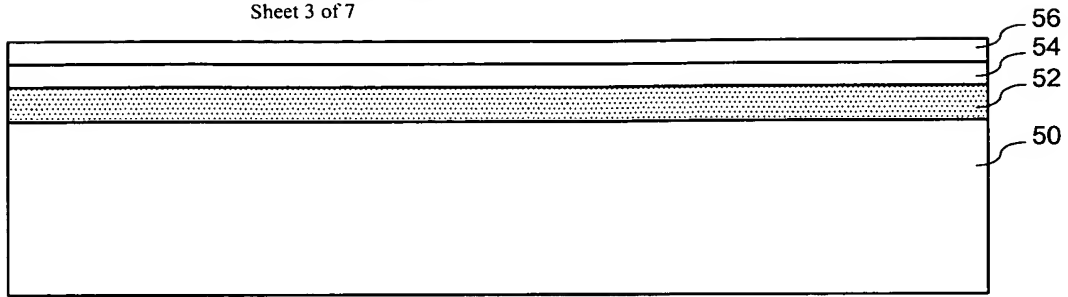
STRAINED SILICON MOSFET HAVING  
REDUCED LEAKAGE AND METHOD OF ITS  
FORMATION

Inventors: Qi Xiang et al.

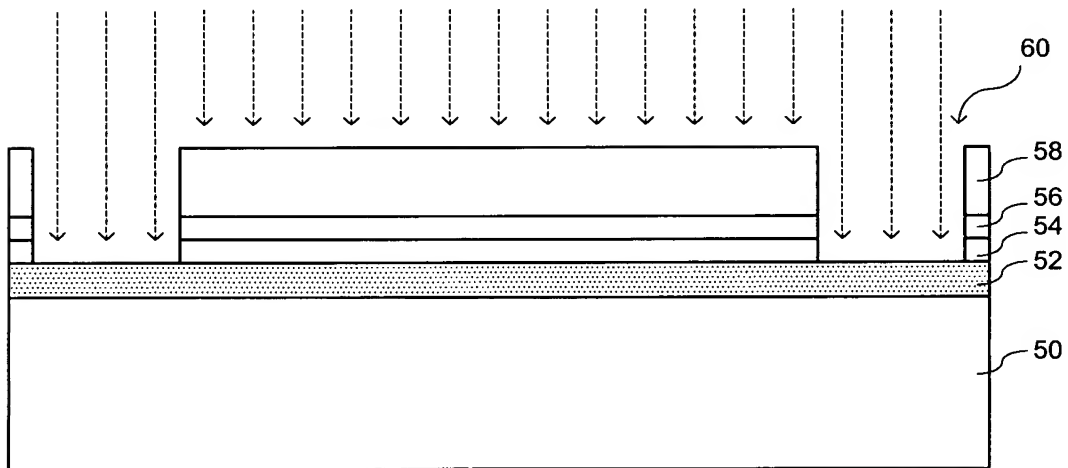
Attorney: Ronald Coslick – 039153-0668

FOLEY & LARDNER – (310) 277-2223

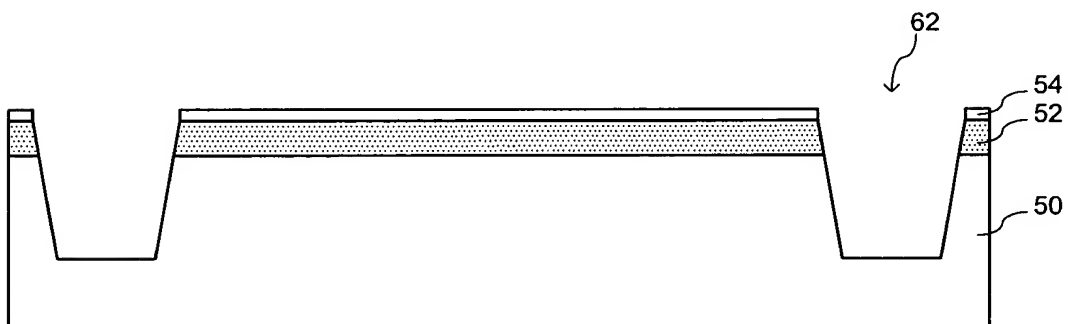
Sheet 3 of 7



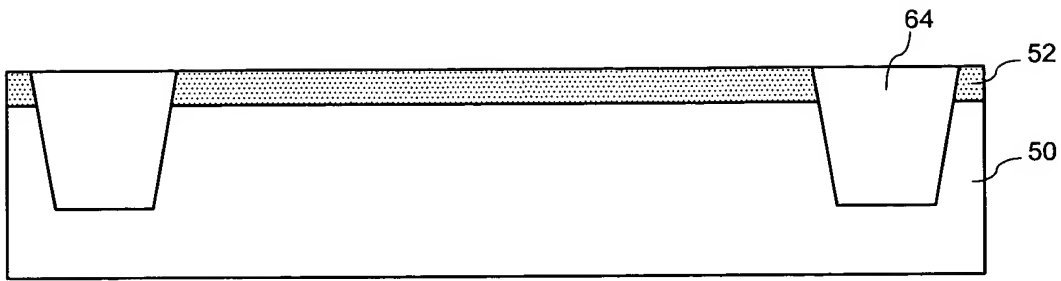
**Figure 3a**



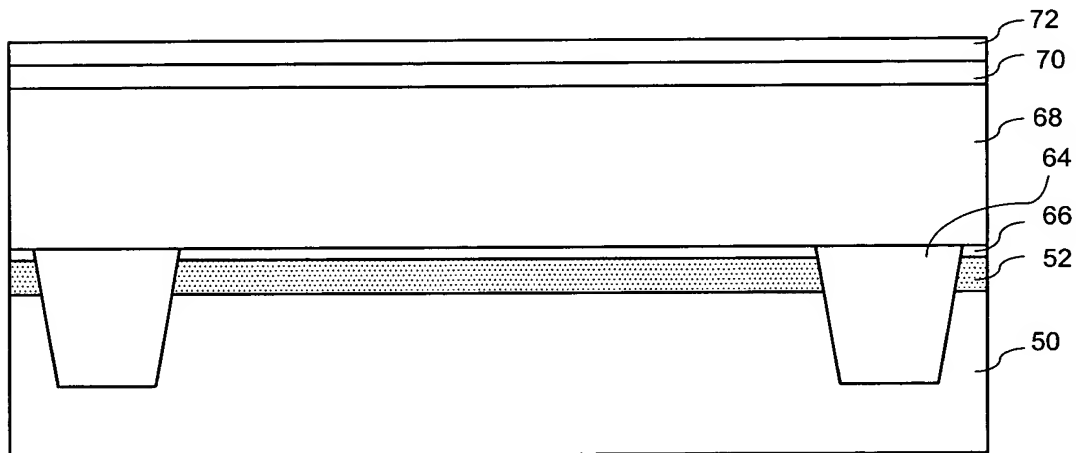
**Figure 3b**



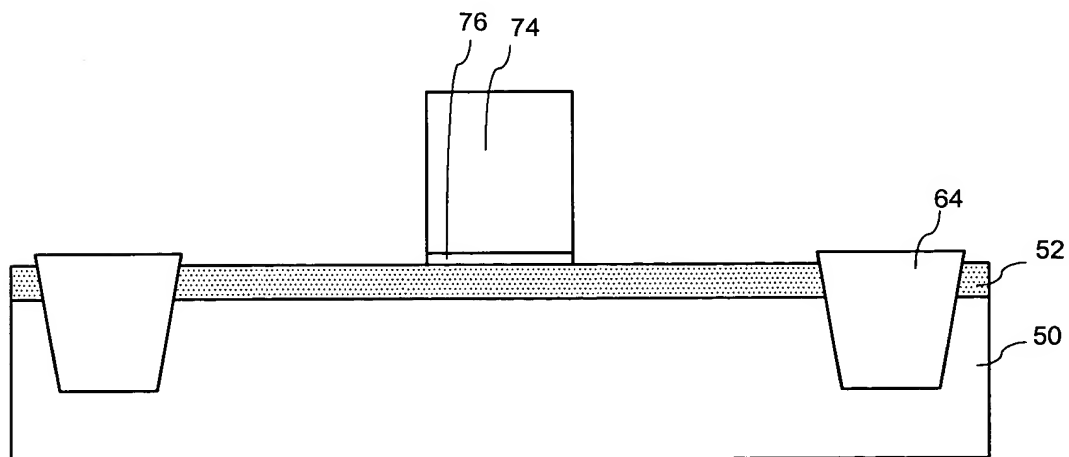
**Figure 3c**



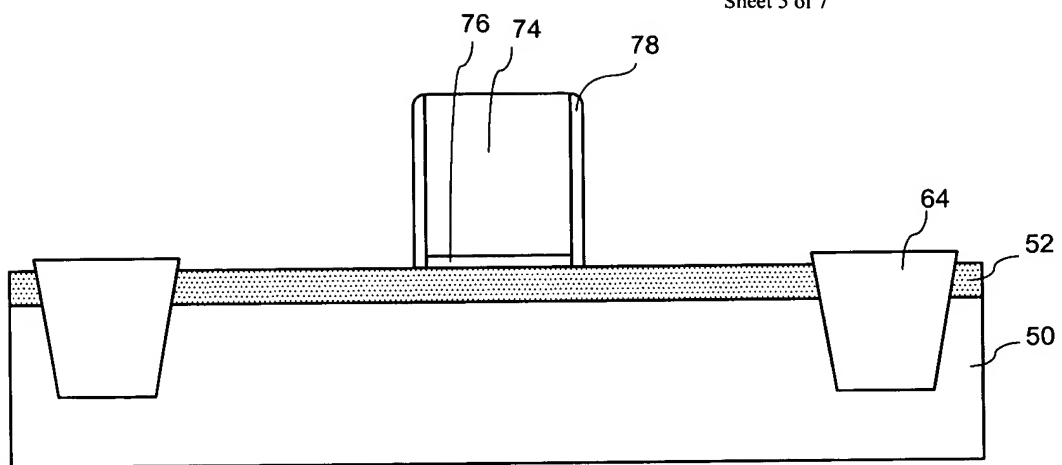
**Figure 3d**



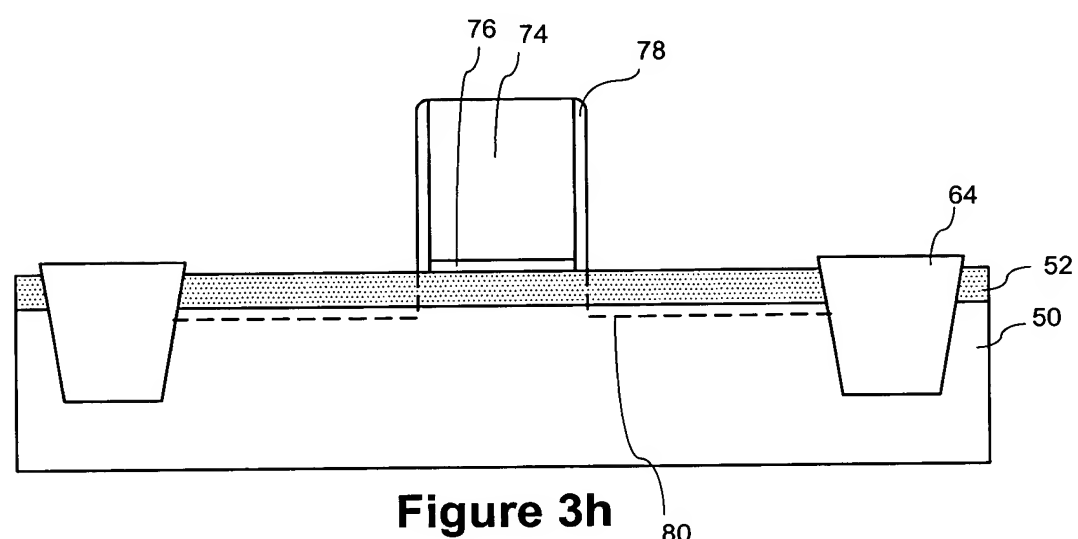
**Figure 3e**



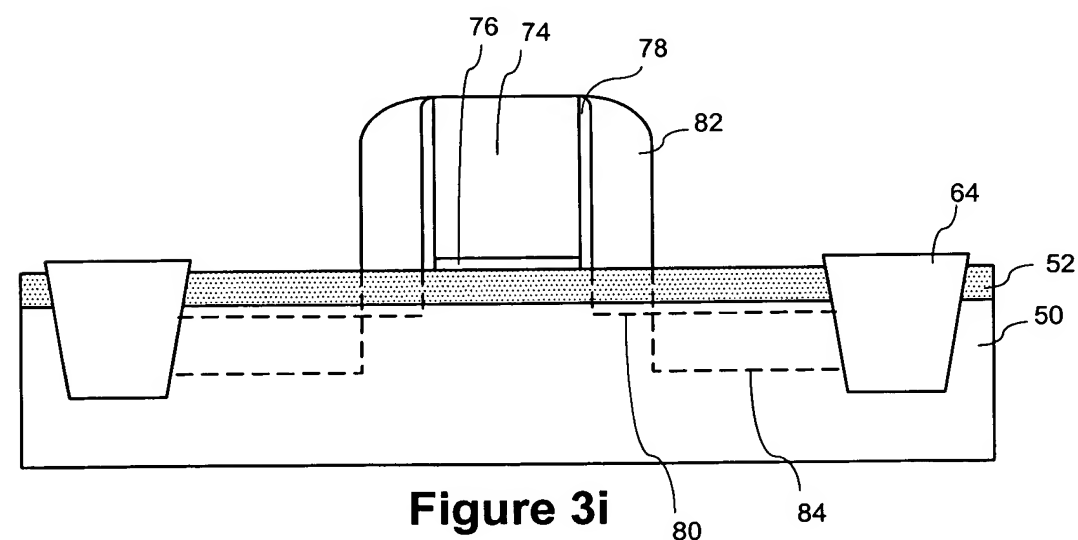
**Figure 3f**



**Figure 3g**



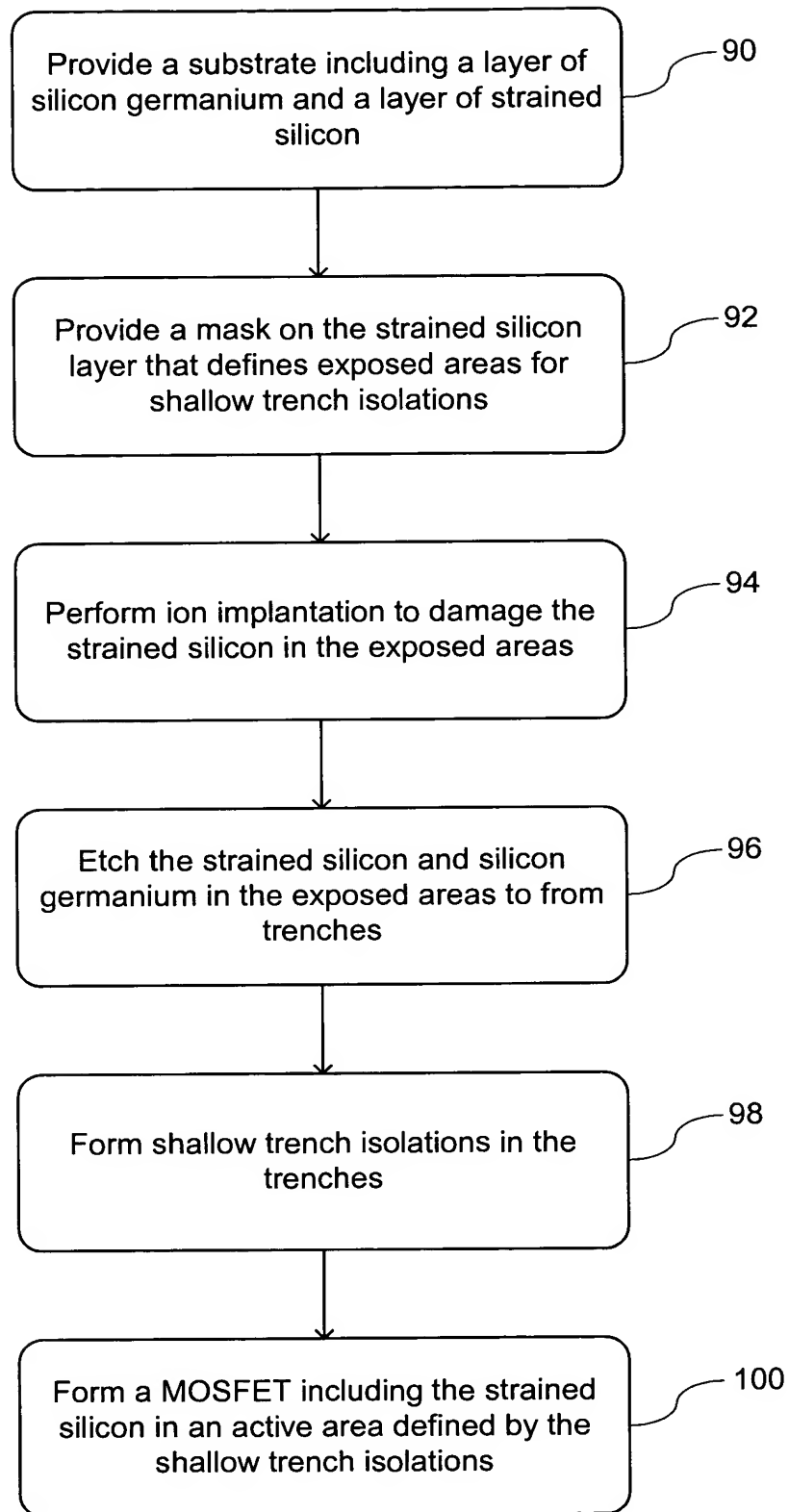
**Figure 3h**



**Figure 3i**

## Sheet 6 of 7





**Figure 4**